(19) World Intellectual Property Organization International Bureau



(43) International Publication Date 25 January 2001 (25.01.2001)

PCT

(10) International Publication Number WO 01/06647 A1

(51) International Patent Classification7: H01L 41/08

H03H 9/17,

(74) Agent: BERGGREN OY AB; P.O. Box 16, FIN-00101 Helsinki (FI).

- (21) International Application Number: PCT/FI00/00591
- (22) International Filing Date:

29 June 2000 (29.06.2000)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data: 991619

19 July 1999 (19.07.1999) FI

- (71) Applicant (for all designated States except US): NOKIA MOBILE PHONES LTD. [FI/FI]; Keilalahdentie 4, FIN-02150 Espoo (FI).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): KAITILA, Jyrki [FI/FI]; 4. Linja 14 B 45, FIN-00530 Helsinki (FI). YLIL-AMMI, Markku [FI/FI]; Peräsin 2A, FIN-02320 Espoo (FI). ELLÄ, Juha [FI/FI]; Kääriäisentie 5, FIN-24800 Halikko (FI).

- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ,
- TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW. (84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian

NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM,

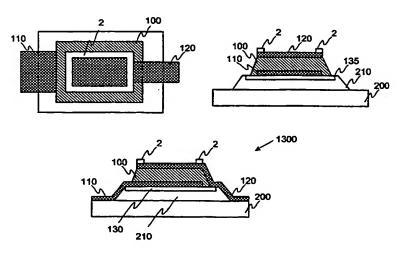
patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published:

With international search report.

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: RESONATOR STRUCTURE AND A FILTER COMPRISING SUCH A RESONATOR STRUCTURE



(57) Abstract: A resonator structure (1200, 1300, 1400), where a certain wave mode is piezoelectrically excitable, comprises at least two conductor layers (110, 120) and at least one piezoelectric layer (110) in between the conductor layers, said conductor layers and piezoelectric layer extending over a first area of the resonator structure, which first area is a piezoelectrically excitable area of the resonator structure. The resonator structure is characterized in that it comprises a frame-like zone (2, 4) confining a center area (3) within the first area, a cut-off frequency of the piezoelectrically excited wave mode in the layer structure of the frame-like zone is different from that in the layer structure of the center area, and width of the frame-like zone and acoustical properties of the layer structure in the frame-like zone are arranged so that displacement relating to the piezoelectrically excited strongest resonance mode is substantially uniform in the center area of the resonator.

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